



**ZVP4525G** 

#### 250V P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C	
-250V	14Ω @ V <sub>GS</sub> = 10V	-265mA	

### **Description**

This new generation trench MOSFET features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

### **Applications**

- · Earth Recall and Dialling Switches
- · Electronic Hook Switches
- · High Voltage Power MOSFET Drivers
- · Telecom Call Routers
- Solid State Relays

## **Features and Benefits**

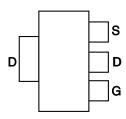
- High Voltage
- Low On-resistance
- Fast Switching Speed
- Low Gate Drive
- Low Threshold
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

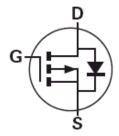
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (e3)
- Weight: 0.112 grams (Approximate)







Pin Out - Top



**Equivalent Circuit** 

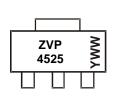
# **Ordering Information** (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZVP4525GTA	ZVP4525	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



**SOT223** 

ZVP4525 = Product Type Marking Code YWW = Date Code Marking Y or Y = Last Digit of Year (ex: 5 = 2015) WW or WW = Week Code (01~53)

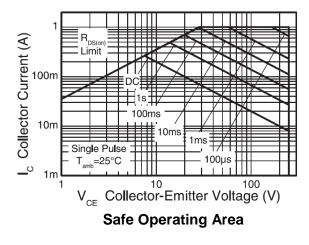


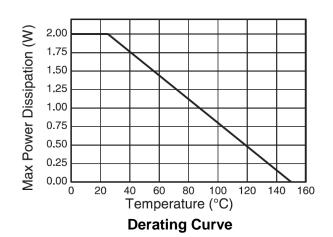
# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

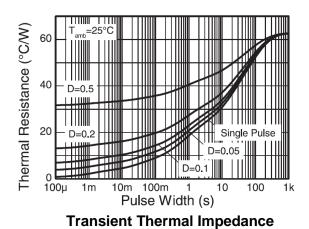
Characteristic	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-250	V
Gate-Source Voltage	$V_{GSS}$	±40	V
Continuous Drain Current $@V_{GS} = 10V$ ; $T_A = +25$ °C (Note 5) $@V_{GS} = 10V$ ; $T_A = +70$ °C (Note 5)	I <sub>D</sub>	-265 -212	mA
Pulsed Drain Current (Note 7)	I <sub>DM</sub>	-1	Α
Continuous Source Current (Body Diode)	Is	-0.75	Α
Pulsed Source Current (Body Diode)	I <sub>SM</sub>	-1	A

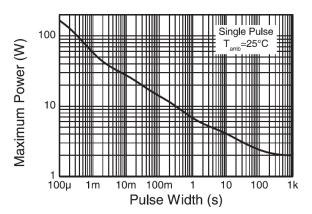
#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T <sub>A</sub> = +25°C (Note 5)	D <sub>-</sub>	2.0	W
Linear Derating Factor	P <sub>D</sub>	16	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	63	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	26	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C









**Pulse Power Dissipation** 



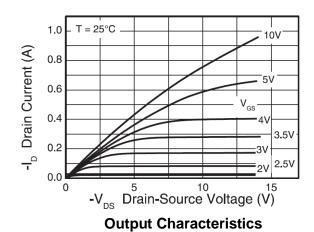
#### Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

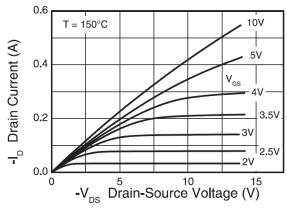
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-250	-285	-	V	$V_{GS} = 0V$ , $I_D = -1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-30	-500	nA	$V_{DS} = -250V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	±1	±100	nA	$V_{GS} = \pm 40V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.8	-1.5	-2.0	V	$V_{DS} = V_{GS}$ , $I_D = -1mA$	
Static Drain Course On Registeres (Note 9)	_	-	10	14	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -200mA	
Static Drain-Source On-Resistance (Note 8)	R <sub>DS(ON)</sub>	-	13	18	Ω	V <sub>GS</sub> = -3.5V, I <sub>D</sub> = -100mA	
Forward Transconductance (Note 10)	<b>g</b> fs	80	200	-	mS	V <sub>DS</sub> = -10V, I <sub>D</sub> = -0.15A	
Diode Forward Voltage (Note 8)	V <sub>SD</sub>	-	-	0.97	V	I <sub>S</sub> = -200mA, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C	
DYNAMIC CHARACTERISTICS			_				
Input Capacitance (Note 10)	C <sub>iss</sub>	-	73	-	pF	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance (Note 10)	Coss	-	12.8	-	pF		
Reverse Transfer Capacitance (Note 10)	C <sub>rss</sub>	-	3.91	-	pF	T = 1.0WHZ	
Total Gate Charge (Notes 9 &10)	Qg	-	2.45	3.45	nC		
Gate-Source Charge (Notes 9 &10)	Q <sub>gs</sub>	-	0.22	0.31	nC	$V_{GS} = -10V, V_{DS} = -25V$ $I_{D} = -200\text{mA}$	
Gate-Drain Charge (Notes 9 &10)	Q <sub>gd</sub>	-	0.45	0.63	nC		
Turn-On Delay Time (Notes 9 & 10)	t <sub>D(ON)</sub>	-	1.53	-	ns		
Turn-On Rise Time (Notes 9 & 10)	t <sub>R</sub>	-	3.78	-	ns	$V_{DD} = -30V$ , $I_{D} = -200$ mA, $V_{GS} = -$	
Turn-Off Delay Time (Notes 9 & 10)	t <sub>D(OFF)</sub>	-	17.5	-	ns	10V, $R_G = 50\Omega$	
Turn-Off Fall Time (Notes 9 & 10)	t <sub>F</sub>	-	7.85	-	ns	]	
Reverse Recovery Time (Note 10)	t <sub>RR</sub>	-	205	290	ns	I <sub>F</sub> = -200mA, di/dt = 100A/µs,	
Reverse Recovery Charge (Note 10)	Q <sub>rr</sub>	-	21	29	nC	$T_J = +25$ °C	

Notes:

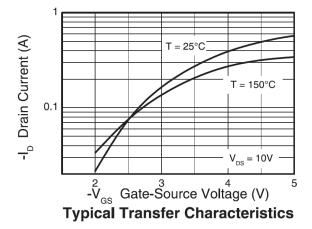
- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
  6. For a device surface mounted on FR4 PCB measured at t ≤ 5 secs.
  7. Repetitive rating 25mm x 25mm FR4 PCB, D=0.02 pulse width=300µs pulse width limited by maximum junction temperature.

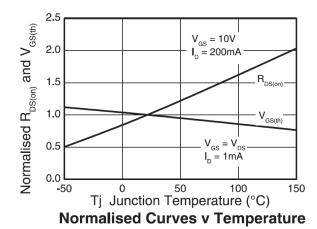
- 8. Measured under pulsed conditions. Pulse width  $\leq$  300µs; duty cycle  $\leq$  2%.
- 9. Switching characteristics are independent of operating junction temperature.
- 10. For design aid only, not subject to production testing.

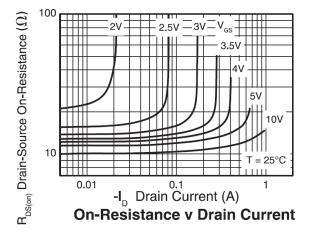


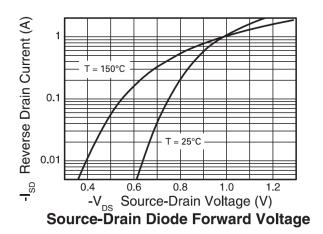


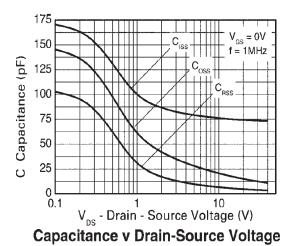


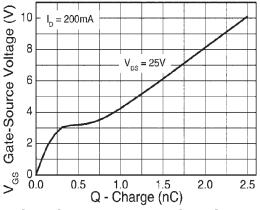








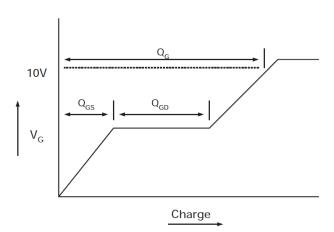




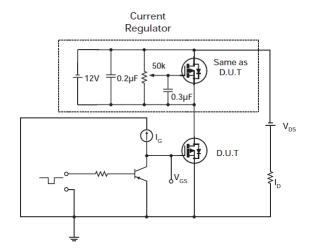
Gate-Source Voltage v Gate Charge



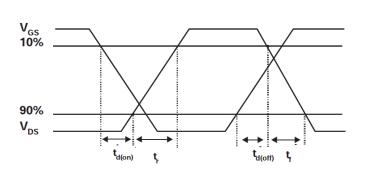
# **Test Circuits**



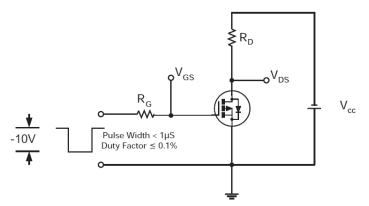
**Basic Gate Charge Waveform** 



**Gate Charge Test Circuit** 



**Switching Time Waveforms** 

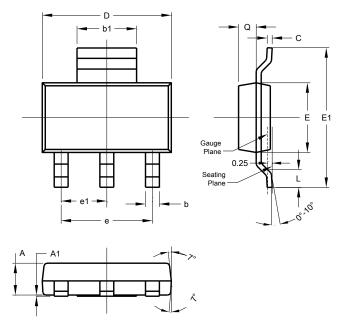


**Switching Time Test Circuit** 



# **Package Outline Dimensions**

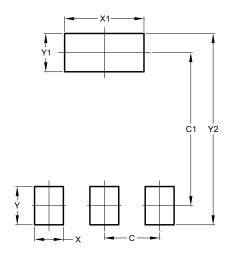
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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